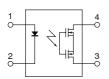


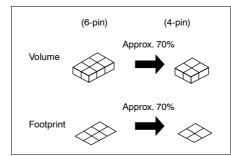




mm inch



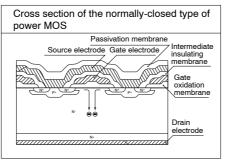
Super miniature design, SOP (1 Form B) 4-pin type. **Controls load voltage** 60V, 350V, 400V.



3. Normally closed type (1 Form B) is low on-resistance. (All AQO4 PhotoMOS are Form B

types. And also the Form A types have a low on-resistance.)

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Doublediffused and Selective Doping) method.



4. Tape and reel

The device comes standard in a tape and reel (1,000 pcs./reel) to facilitate automatic insertion machines.

5. Controls low-level analog signals PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

TYPE	S							
Туре	Output rating*		Dealisers		Part No.	Packing quantity		
	Load voltage	Load current	Package size	Tube packing style	Tape and reel	packing style	Tube	Tape and reel
AC/DC type	60V	500mA		AQY412S	AQY412SX (Picked from the 1/2-pin side)	AQY412SZ (Picked from the 3/4-pin side)		1,000 pcs.
	350V	120mA	SOP4pin	AQY410S	AQY410SX (Picked from the 1/2-pin side)	AQY410SZ (Picked from the 3/4-pin side)	1 tube contains: 100 pcs. 1 batch contains: 2,000 pcs.	
	400V	100mA		AQY414S	AQY414SX (Picked from the 1/2-pin side)	AQY414SZ (Picked from the 3/4-pin side)	- 2,000 pcs.	

* Indicate the peak AC and DC values.

Note: For space reasons, the initial letters of the part number "AQY", the SMD terminal shape indicator "S" and the packaging style indicator "X" or "Z" are not marked on the relay. (Ex. the label for product number AQY414S is 414)

GU PhotoMO (AQY41C

6. Low-level off-state leakage current In contrast to the SSR with an off-state leakage current of several milliamperes, the PhotoMOS relay features a very small off state leakage current of 1nA even with the rated load voltage of 400 V (AQY414S).

TYPICAL APPLICATIONS

- Power supply
- Measuring equipment
- Security equipment
- Telephone equipment
- Sensors

FEATURES

1. 60V type couples high capacity (0.5A) with low on-resistance (1 Ω).

Item	GU SOP type			
Part No.	AQY410S	AQY412S		
Load voltage	350V	60V		
Continuous load current	0.12A	0.5A		
ON resistance (typ.)	18Ω	1Ω		

2. SO package 4-pin type in super miniature design

The device comes in a super-miniature SO package 4-pin type measuring (W) 4.3×(L) 4.4×(H) 2.1 mm (W) .169×(L) .173×(H) .083 inch —approx. 70% of the volume and 70% of the footprint size of SO package 6-pin type PhotoMOS relays.

GU PhotoMOS (AQY41OS)

RATING

AC/DC type

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

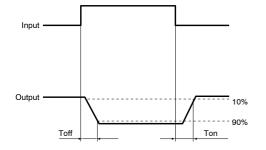
	Item	Symbol	AQY412S	AQY410S	AQY414S	Remarks
Input	LED forward current	IF	50 mA			
	LED reverse voltage	Vr	V _R 5 V			
	Peak forward current	FP	IFP 1 A			f = 100 Hz, Duty factor = 0.1%
	Power dissipation	Pin	75 mW			
Output	Load voltage (peak AC)	VL	60 V	350 V	400 V	
	Continuous load current (peak AC)	IL.	0.5 A	0.12 A	0.1 A	
	Peak load current	Ipeak	1.5 A	0.3 A	0.24 A	100ms (1 shot), V∟ = DC
	Power dissipation	Pout	300 mW			
Total power dissipation		PT	350 mW			
I/O isolation voltage		Viso	1,500 V AC			
Temperture limits	Operating	Topr	-40°C to +85°C -40°F to +185°F			Non-condensing at low temperatures
	Storage	Tstg	-40°C to +100°C -40°F to +212°F			

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

	Item		Symbol	AQY412S	AQY410S	AQY414S	Remarks
	LED operate (OFF) current	Typical	1	0.9 mA			l∟ = Max.
		Maximum	Foff	3 mA			
	LED reverse (ON) current	Minimum	-		l∟ = Max.		
Input		Typical	Fon	0.85 mA			
	LED dropout voltage	Typical	VF	1.25 V (1.14 V at I⊧ = 5 mA)			I⊧ = 50 mA
		Maximum	VF	1.5 V			
	On resistance	Typical	- Ron -	1 Ω	18 Ω	26 Ω	I⊧ = 0 mA I∟ = Max. Within 1 s on time
Output		Maximum	Kon	2.5 Ω	25 Ω	35 Ω	
	Off state leakage current	Maximum	ILeak	1 μΑ			I⊧ = 5 mA V∟ = Max.
	Operate (OFF) time*	Typical	Toff	0.9 ms	0.52 ms	0.47 ms	IF = 0 mA > 5 mA
		Maximum	I off	3 ms 1 ms		I∟ = Max.	
	Reverse (ON) time*	Typical	Ton	0.21 ms	0.23 ms	0.28 ms	$I_F = 5 \text{ mA} > 0 \text{ mA}$
Transfer		Maximum	Ion	1 ms	1 ms		I∟ = Max.
characteristics	I/O capacitance	Typical	0	0.8 pF			f = 1 MHz Vв = 0 V
		Maximum	Ciso	1.5 pF			
	Initial I/O isola- tion resistance	Minimum	Riso	1,000 MΩ			500 V DC

Note: Recommendable LED forward current $I_F = 5mA$.

*Operate/Reverse time



Dimensions
Schematic and Wiring Diagrams
Cautions for Use

Type of connection

GU PhotoMOS (AQY41OS)

REFERENCE DATA

1. Load current vs. ambient temperature characteristics

Allowable ambient temperature:

-40°C to +85°C



characteristics

1.0

٤_{0.8}

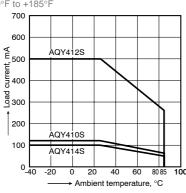
20.6

Beverse 0.4

0.2

0

time



4. Reverse (ON) time vs. ambient temperature

AQY414S

Ambient temperature, °C

AQY410S

60 80 85 100

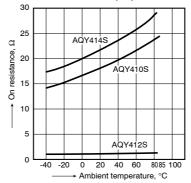
LED current: 5 mA; Load voltage: Max.(DC);

Continuous load current: Max.(DC)

2. On resistance vs. ambient temperature characteristics

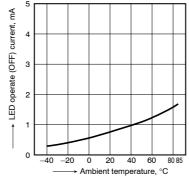
Measured portion: between terminals 3 and 4:

LED current: 0 mA; Continuous load current: Max.(DC)



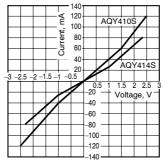
5. LED operate (OFF) current vs. ambient temperature characteristics

Sample: All types; Load voltage: Max.(DC); Continuous load current: Max.(DC)



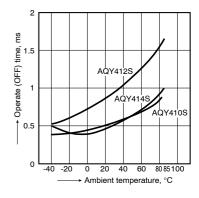
8-(1). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 3 and 4: Ambient temperature: 25°C 77°F



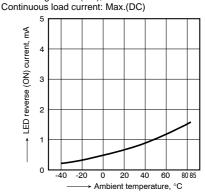
3. Operate (OFF) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max.(DC); Continuous load current: Max.(DC)



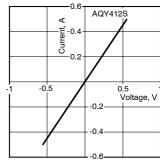
6. LED reverse (ON) current vs. ambient temperature characteristics Sample: All types;

Load voltage: Max.(DC);



8-(2). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 3 and 4; Ambient temperature: 25°C 77°F



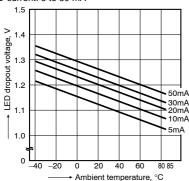
7. LED dropout voltage vs. ambient temperature characteristics Sample: All types;

-40 -20

AQY412S

0 20 40

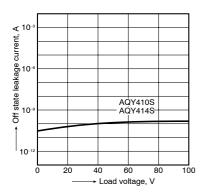
LED current: 5 to 50 mA



GU PhotoMOS (AQY41OS)

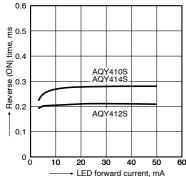
9-(1). Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 3 and 4; LED current: 5 mA; Ambient temperature: 25°C 77°F



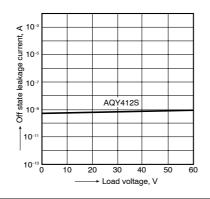
11. Reverse (ON) time vs. LED forward current characteristics

Measured portion: between terminals 3 and 4; Load voltage: Max.(DC); Continuous load current: Max.(DC); Ambient temperature: $25^{\circ}C$ 77°F



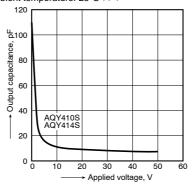
9-(2). Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 3 and 4; LED current: 5 mA; Ambient temperature: $25^{\circ}C$ 77°F



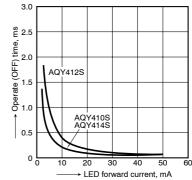
12-(1). Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 3 and 4; Frequency: 1 MHz; Ambient temperature: 25°C 77°F



10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 3 and 4; Load voltage: Max.(DC); Continuous load current: Max.(DC); Ambient temperature: $25^{\circ}C$ $77^{\circ}F$



12-(2). Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 3 and 4; Frequency: 1 MHz; Ambient temperature: 25°C 77°F

600 600

